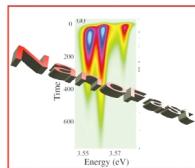


Spettroscopia ottica avanzata di nanostrutture per dispositivi optoelettronici nell'UV

Dipartimento di Fisica ed
Astronomia



7/04/2010

Partecipanti:

2 strutturati Fis (Vinattieri,Gurioli)
+1 strutturato Energ (Bogani)
1 assegnista (Cavigli)
1PhD (Gabrieli, XXV ciclo)
1PhD (Stokker-Cheregi, XXI ciclo)

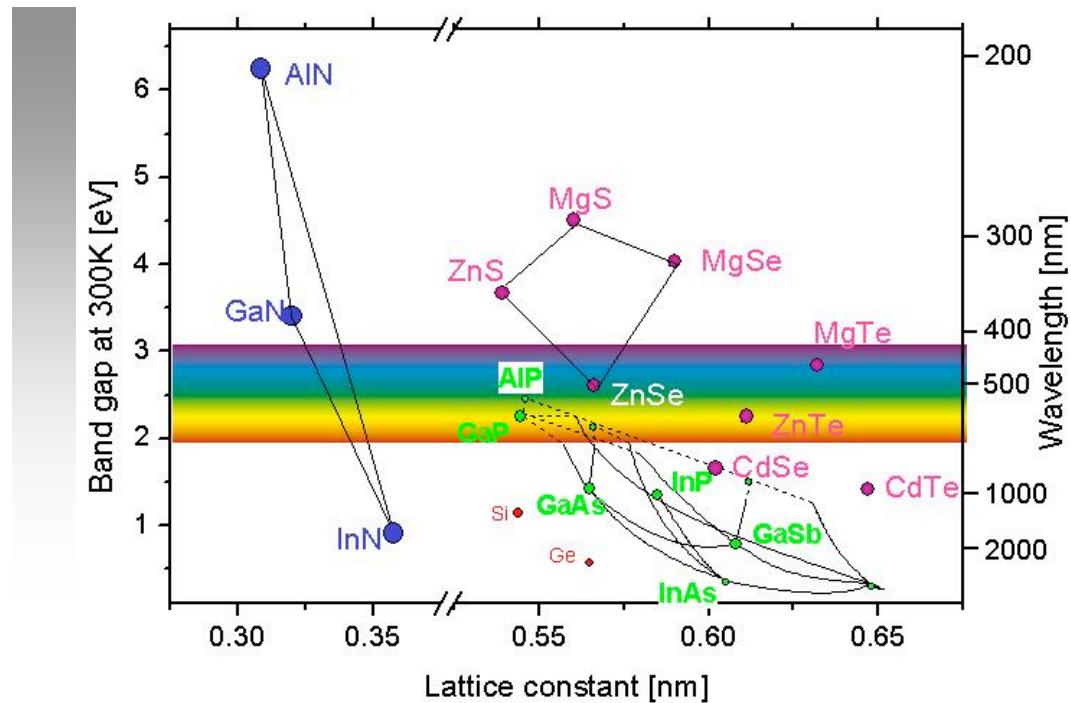
Linee ricerca

High spatial and temporal resolution optical spectroscopy

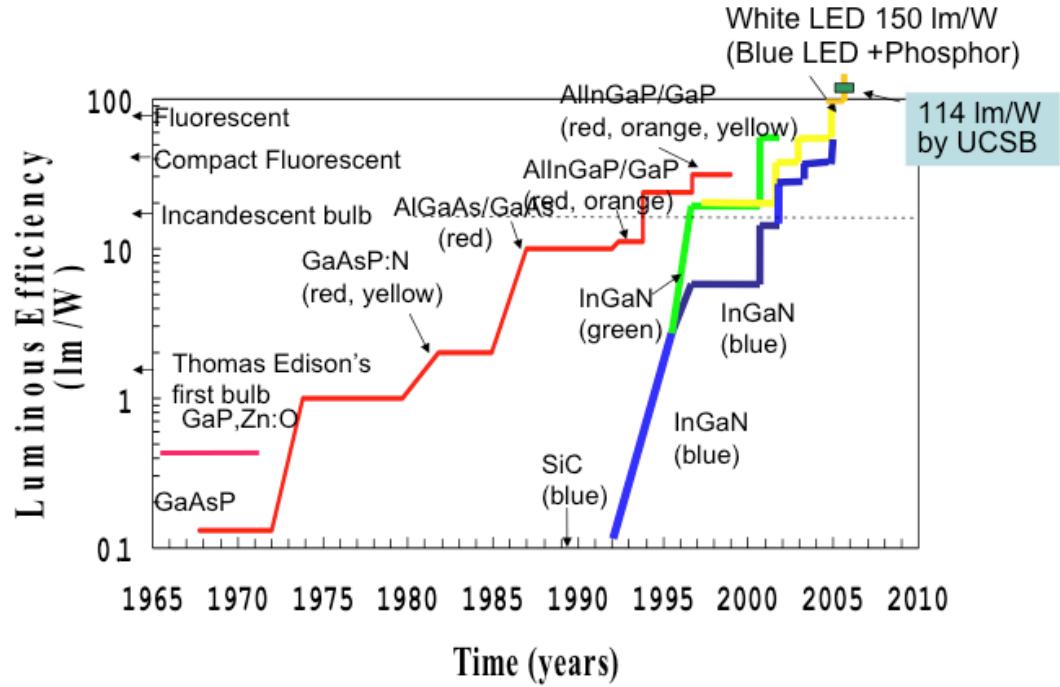
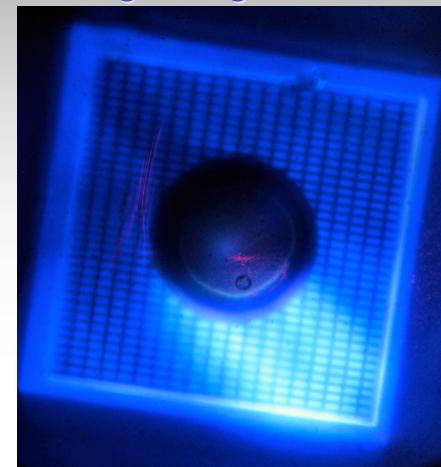
- Nitrides heterostructures (VI programma EU-Clermont2, collaborazioni CHREA-Valbonne, EPFL-Losanna)
- Semiconductor NPs (TiO_2) for innovative photovoltaic energy conversion (DE, PoliTO, CNR & DipFisPI: Richiesta PAR-FAS Regione Toscana)
- GaN optoelectronic devices for future applications (DE, DipIng-PD, CNR-Pr: PRIN)

High resolution optical spectroscopy of Nitride Heterostructures

- GaN bulk μ Cavities for room T polariton lasers
- Exciton dynamics in high quality GaN/AlGaN QWs



Nitrides nicely fit the UV region:
GaN and InN, GaN,AlN ternary-quaternary alloys for high efficiency solid state lightening devices



Advantages:

High tunability NUV-NIR

High radiative efficiency

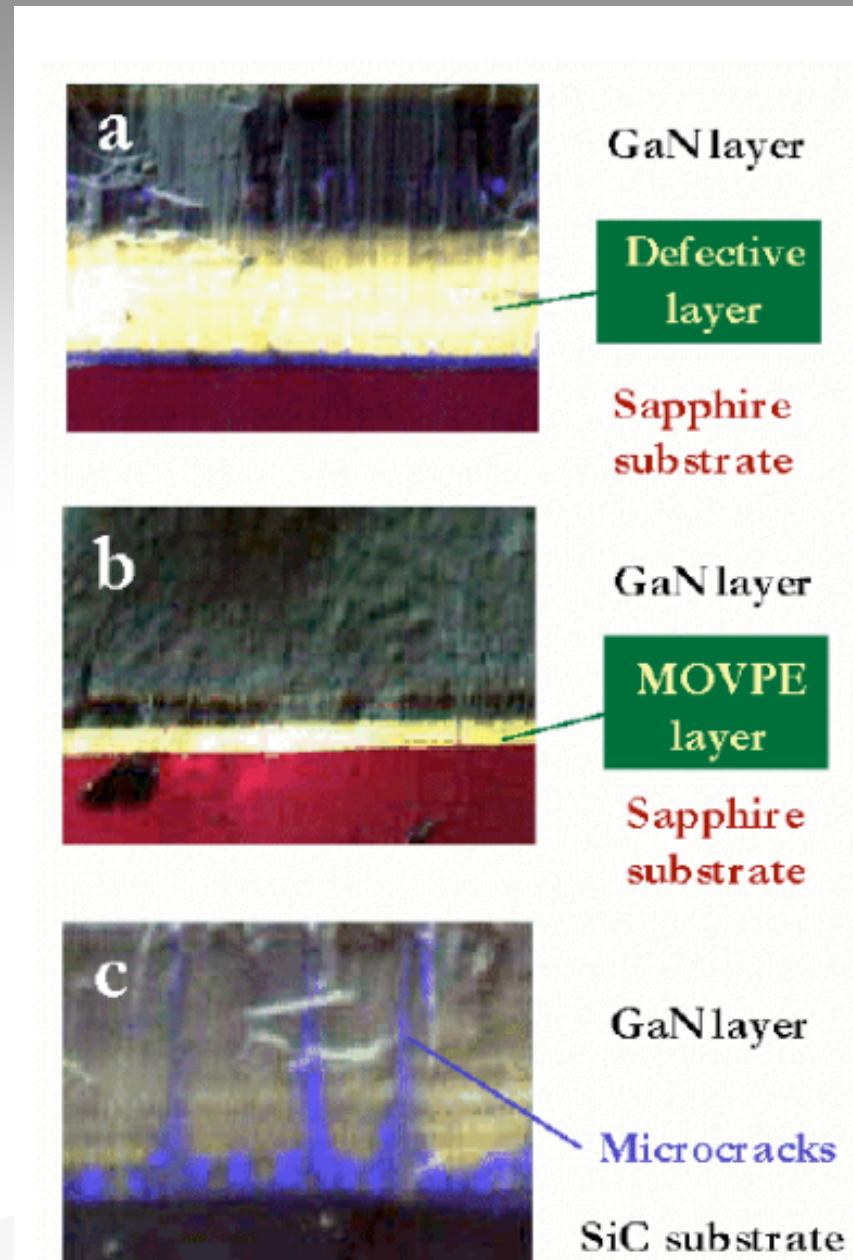
Low maintenance cost

But: poor material quality

- Piezoelectricity
- High content of defects
- Poor control of doping

Dislocation density GaAs on Si:
 $10^4\text{-}10^5\text{ cm}^{-2}$

Dislocation density GaN on Sapphire:
 10^{10} cm^{-2} now 10^7 cm^{-2}



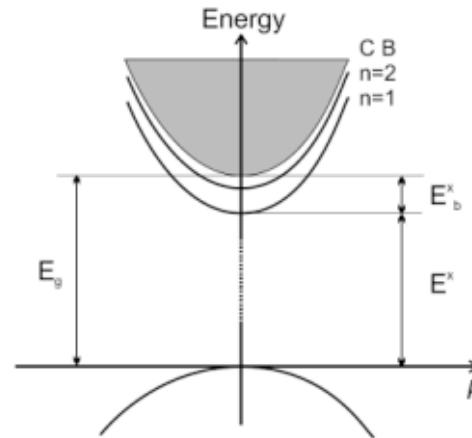
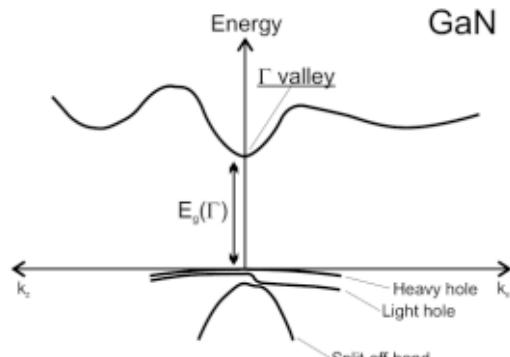
Reducing the defects density



Exciton dynamics

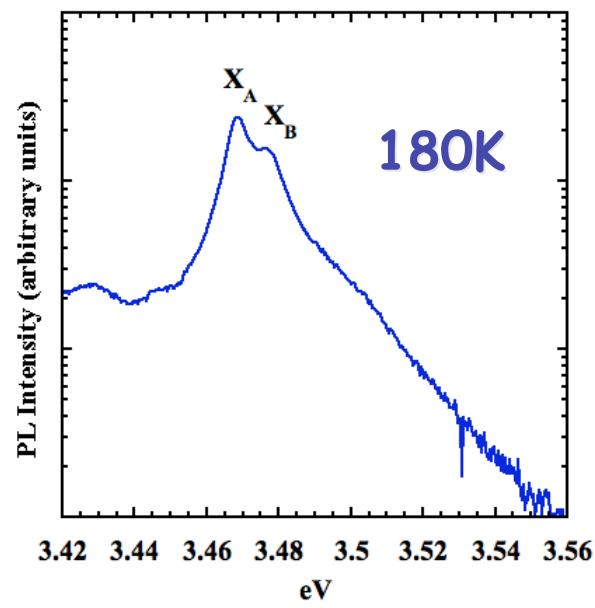
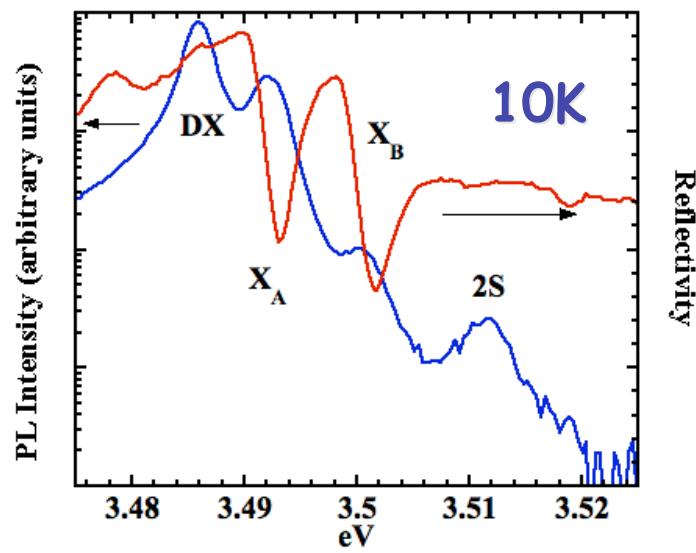
GaN	ZnO	GaAs	CdSe
3.5 eV	3.4 eV	1.5 eV	3.5 eV
25 meV	60meV	4meV	20 meV

Excitons @ RT: new devices

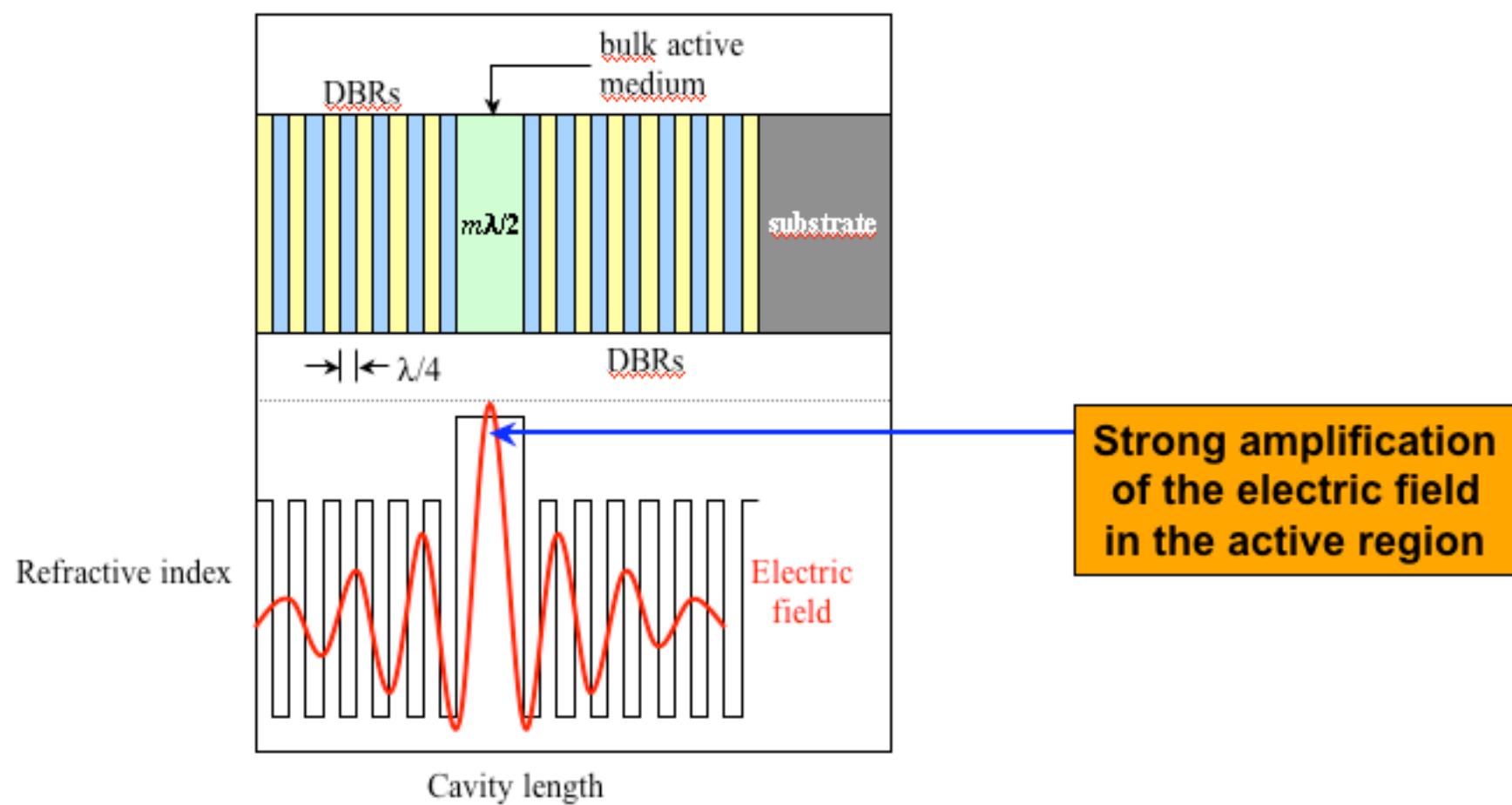


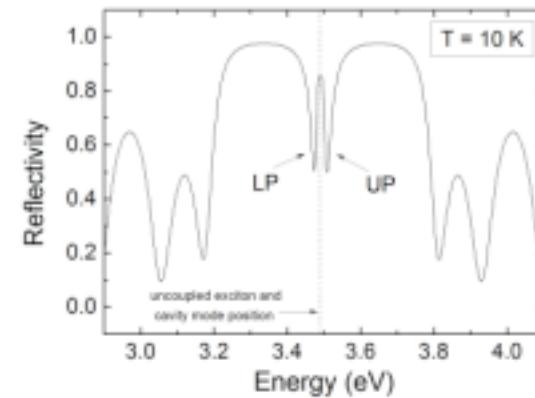
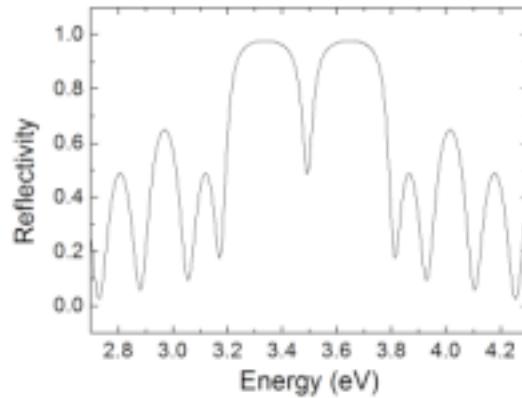
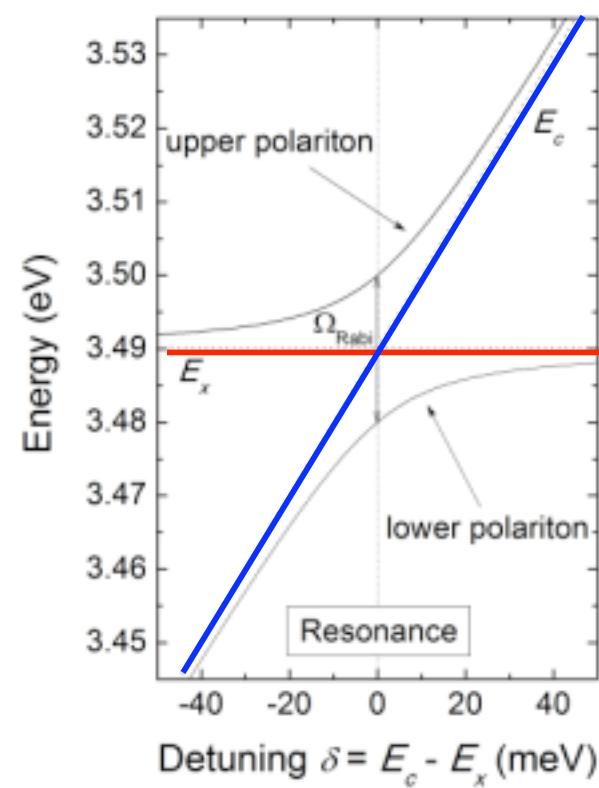
$$E_n^x = E_g - E_b^x \frac{1}{n^2} \quad E_b^x = 13.6 eV \frac{\mu}{\epsilon^2}$$

for bulk GaN:
 $E_b^x \sim 25$ meV



Microcavities: Strong coupling at RT

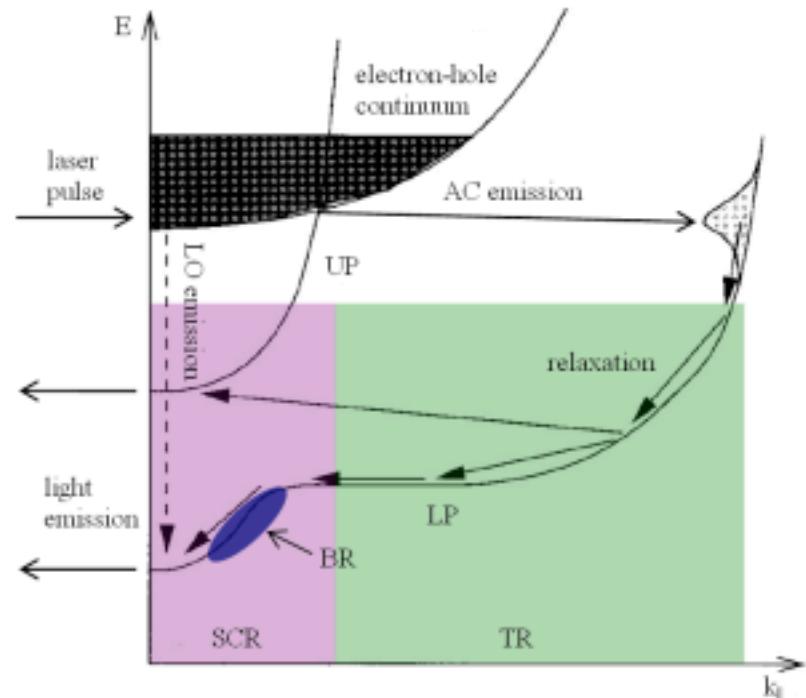
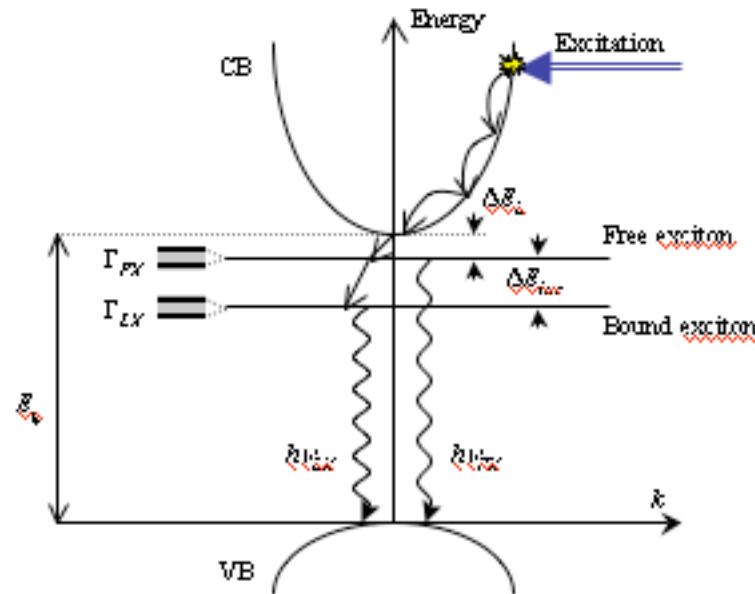




Rabi splitting in GaN-based μ C
50-60 meV : strong coupling
regime @ RT.

Polariton=Boson

Polariton effective mass $\approx 10^{-4}$
exciton mass $\approx 10^{-9}$ Rb mass
→ high T_c



bulk exciton
photoluminescence

strong coupling polariton
photoluminescence

Bose-Einstein Exciton Condensate & Polariton Lasing

(J.Kasprzak et al.: Nature 443, 409 (2006), S.Christopoulos et. al.:PRL 98, 126405 (2007),
G.Christmann et al.: APL 93, 051102 (2008))

Our research focussed on:

- Investigation of SC regime
- Investigation of relaxation bottleneck and thermalization (Exciton-polariton dynamics)

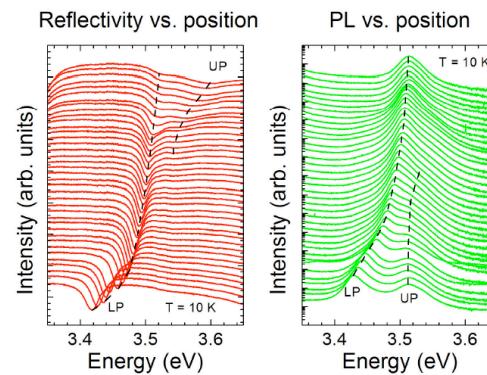
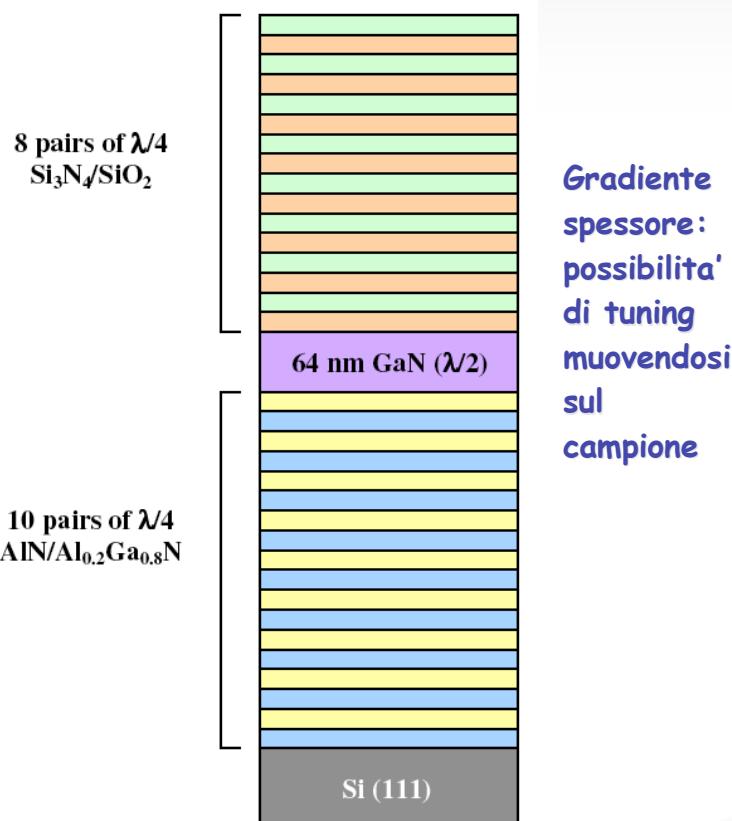


Figure 5.18. Simultaneous reflectivity (left) and TI PL (right) spectra at $T = 10\text{ K}$ of the hybrid microcavity (sample 808) as a function of excitation position. Spectra are shifted in intensity for clarity. The dashed lines are guides to the eye.

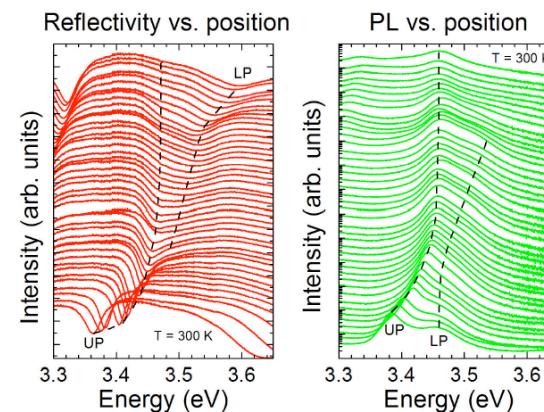


Figure 5.20. Simultaneous reflectivity (left) and TI PL (right) spectra at $T = 300\text{ K}$ of the hybrid microcavity (sample 808) as a function of excitation position. Spectra are shifted in intensity for clarity. The dashed lines are guides to the eye.



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Superlattices and Microstructures 41 (2007) 376–380

Superlattices
and Microstructures

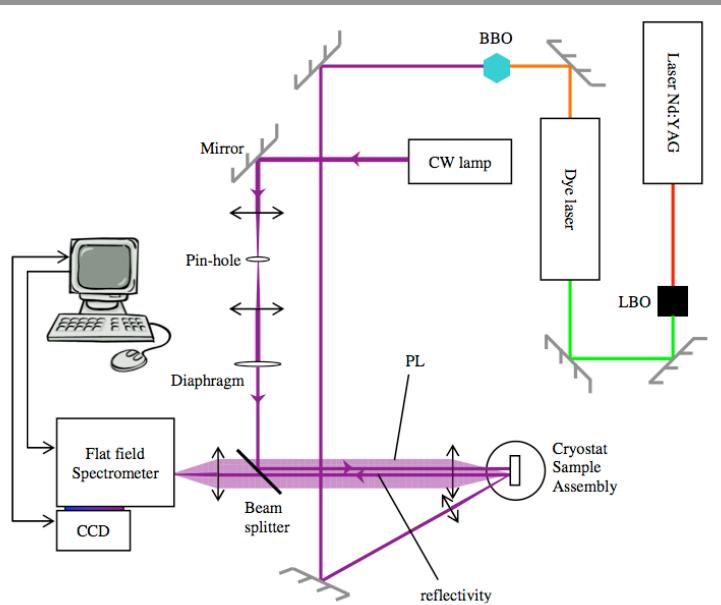
www.elsevier.com/locate/superlattices

Polariton thermalization in GaN microcavities in the strong light-matter coupling regime

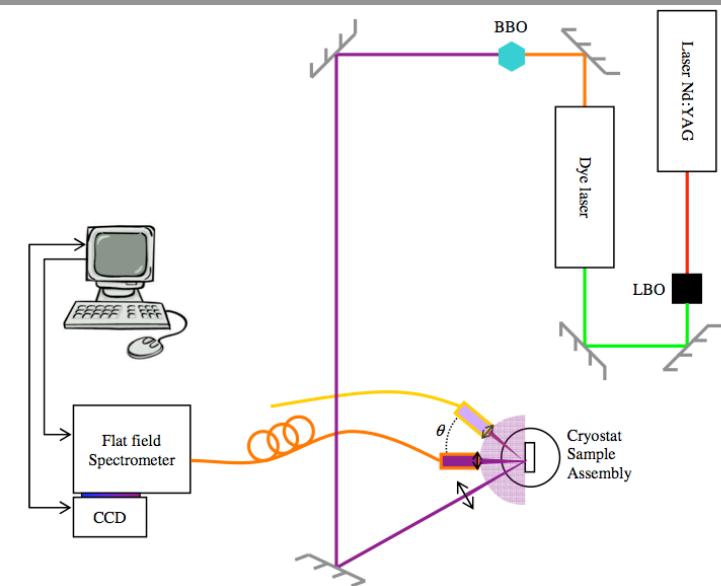
F. Stokker-Cheregi^{a,*}, M. Zamfirescu^a, A. Vinattieri^a, M. Gurioli^a, I. Sellers^b, F. Semond^b, M. Leroux^b, J. Massies^b

^aLENS and Dipartimento di Fisica, Università di Firenze, 50019 Sesto Fiorentino, Italy

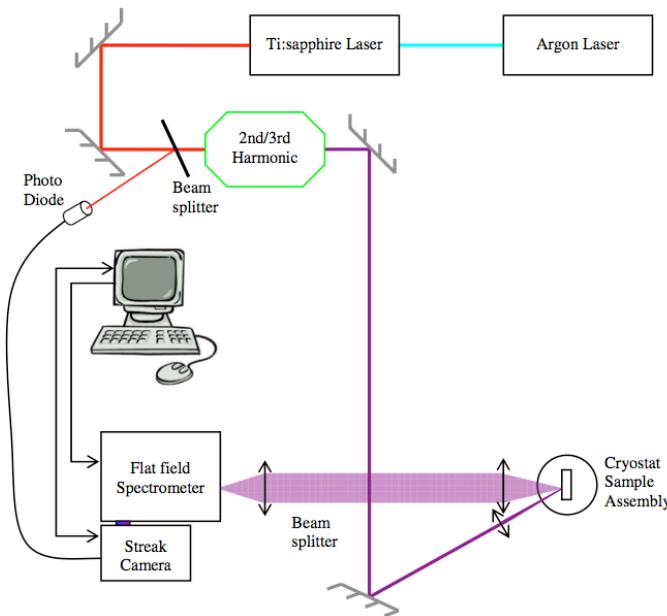
^bCRHEA-CNRS, Rue Bernard Gregory, Valbonne 06560, France



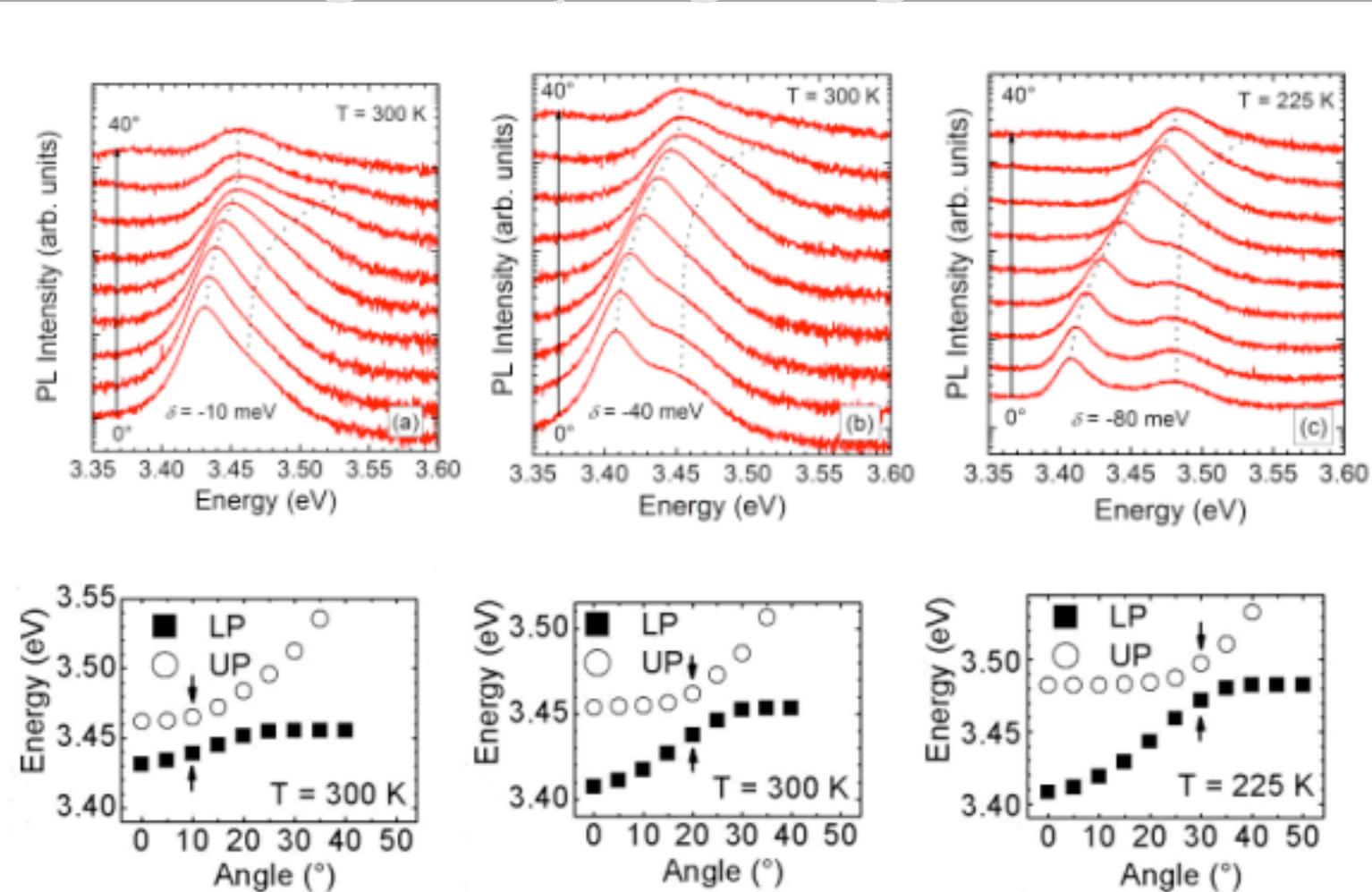
Position-angle
resolved
Reflectivity
& PL



ps Time-resolved PL



Strong Coupling Regime @ RT



PHYSICAL REVIEW B 74, 193308 (2006)

Exp Rabi splitting: 30 meV → SC @ RT

Polariton emission and reflectivity in GaN microcavities as a function of angle and temperature

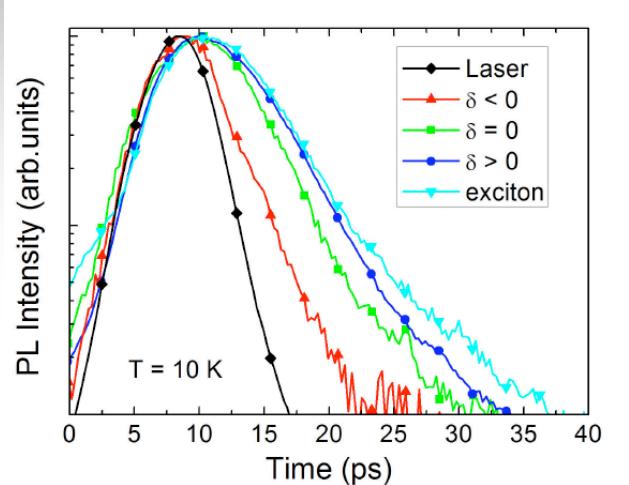
I. R. Sellers,* F Semond, M. Leroux, and J. Massies
CRHEA-CNRS, Rue Bernard Gregory, Valbonne 06560, France

M. Zamfirescu, F. Stokker-Cheregi, M. Gurioli, A. Vinattieri, and M. Colocci
LENZ, Dipartimento di Fisica, Università di Firenze, 50019 Sesto Florentino, Italy

A. Tahraoui and A. A. Khalifa
Department of Physics & Astronomy, Hicks Building, Hounsfield Road, University of Sheffield, S3 7RH, United Kingdom

Dipartimento di Fisica ed
Astronomia

Modification of the Radiative Recombination Rate in presence of SC



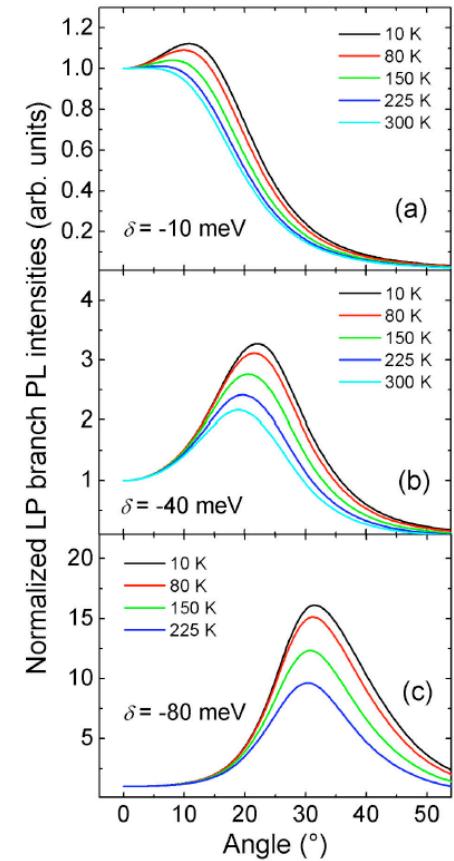
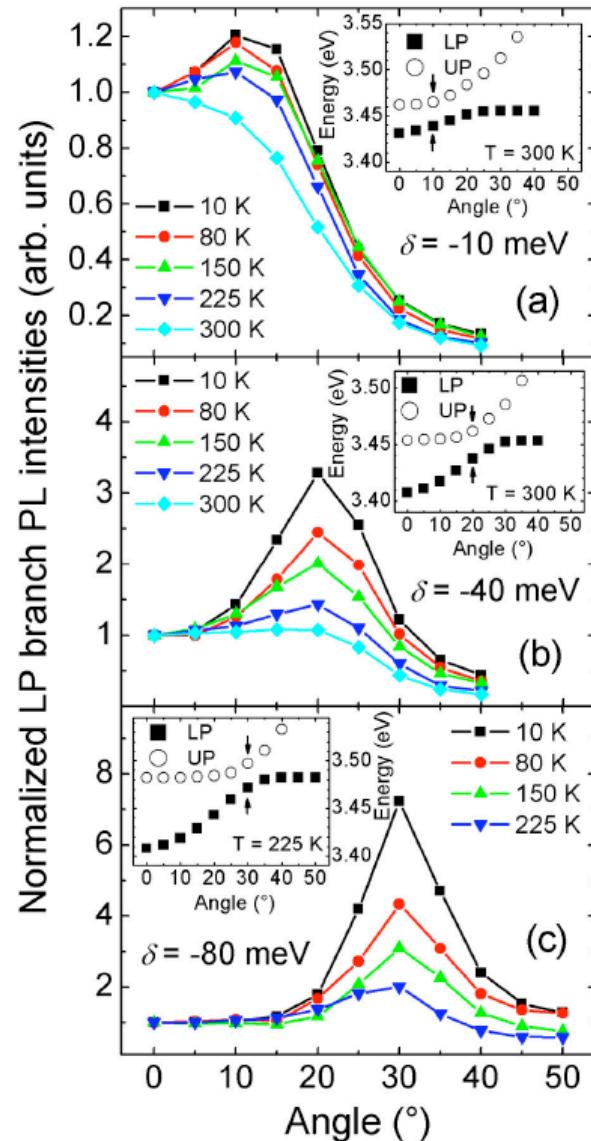
Moreover, the LP and UP populations are thermalized at $T = 300$ K, despite the very short lifetimes. This denotes very efficient energy relaxation processes in the LP, as well as an efficient population of the UP states through acoustic phonon interactions in our bulk GaN microcavity.

APPLIED PHYSICS LETTERS 92, 042119 (2008)

Polariton relaxation bottleneck and its thermal suppression in bulk GaN microcavities

F. Stokker-Cheregi,^{1,a)} A. Vinattieri,¹ F. Semond,² M. Leroux,² I. R. Sellers,² J. Massies,² D. Solnyshkov,³ G. Malpuech,³ M. Coloccia,¹ and M. Gurioli¹
¹LENS and Department of Physics, University of Florence, I-50019 Sesto Fiorentino, Italy
²CRHEA-CNRS, Rue Bernard Gregory, Valbonne 06560, France
³LASEA, CNRS, Université Blaise Pascal, 24, av des Landais, 63177 Aubière, France

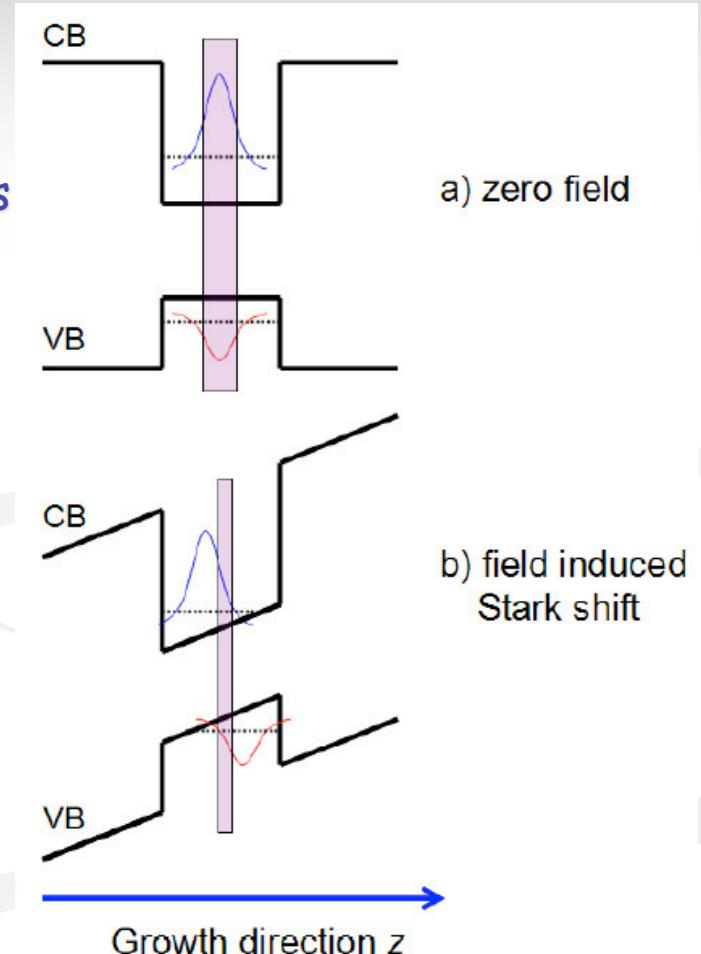
Suppression of Relaxation Bottleneck at RT

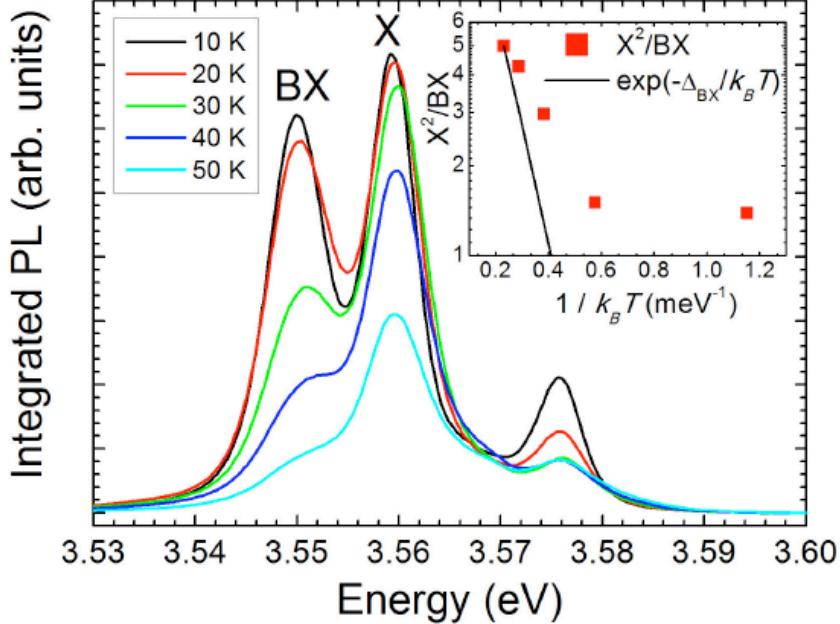


Exciton Dynamics in State-of-the-art GaN/AlGaN SQWs

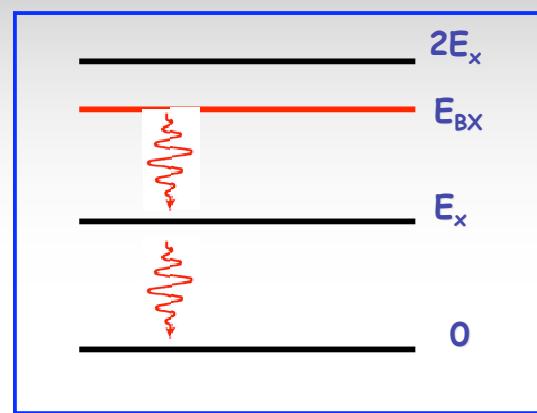
Strain & Internal Electric Field (piezo+ spontaneous polarization up to 1MV/cm) strongly affect the optical properties:

- Reduction of the exciton rad rate (Quantum Confined Stark Effect)
- Inhomogenous broadening
- Exciton localization

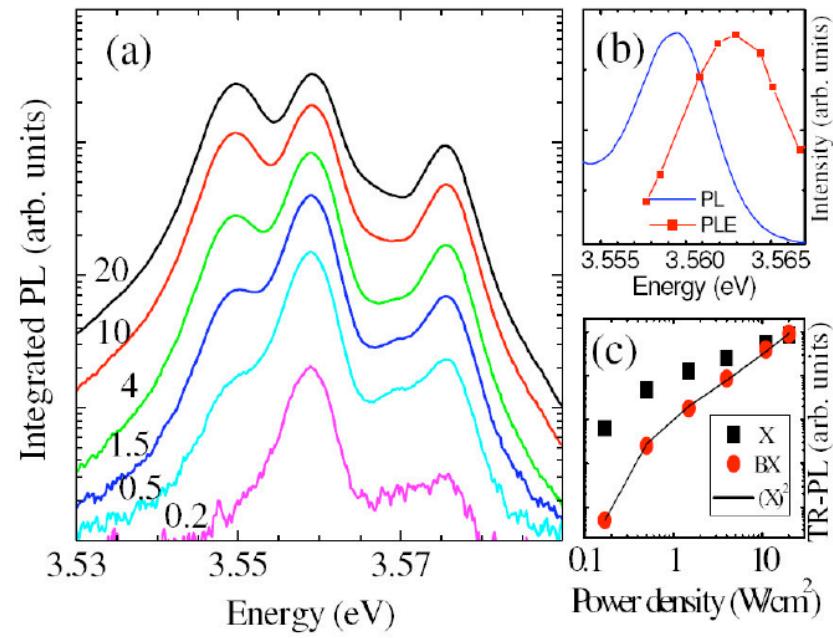


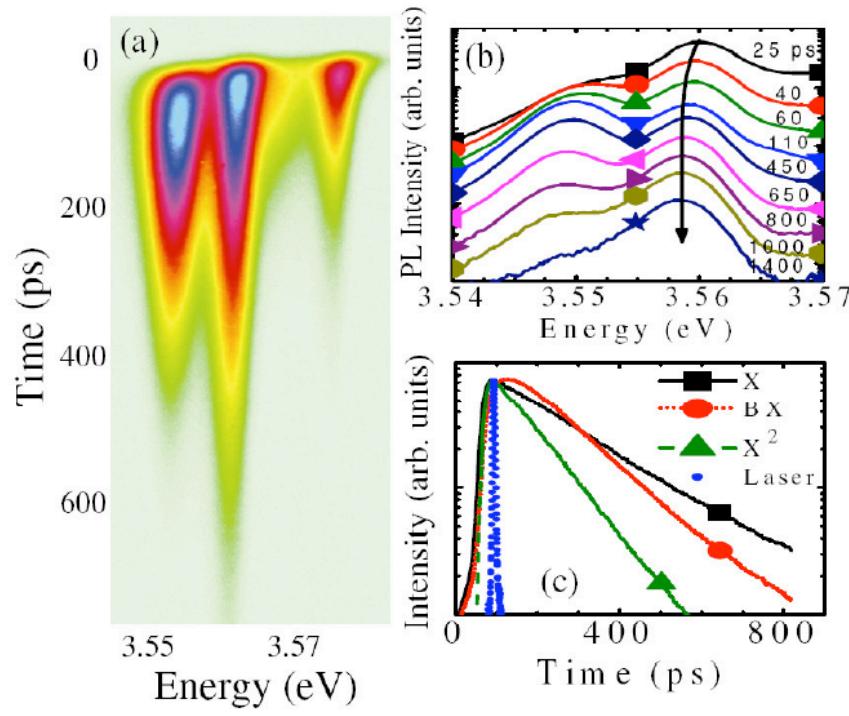


Biexciton Recombination Kinetics



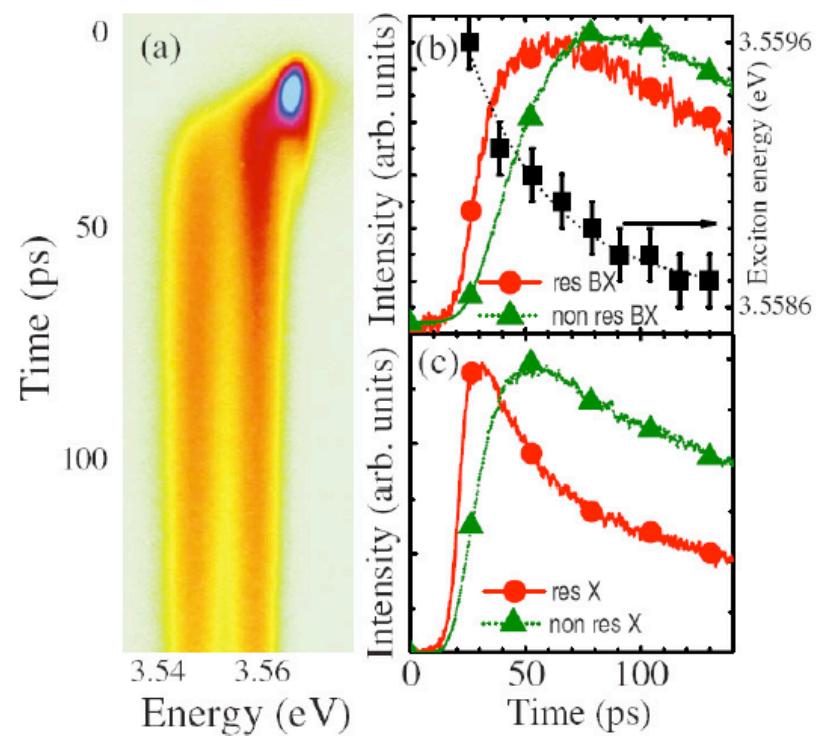
$$\frac{n_X^2}{n_{BX}} \propto \exp(-\Delta_{BX}/k_B T)$$





Non-resonant excitation

Only free excitons give rise to biexcitons: biexciton formation is quenched by exciton localization



Resonant excitation

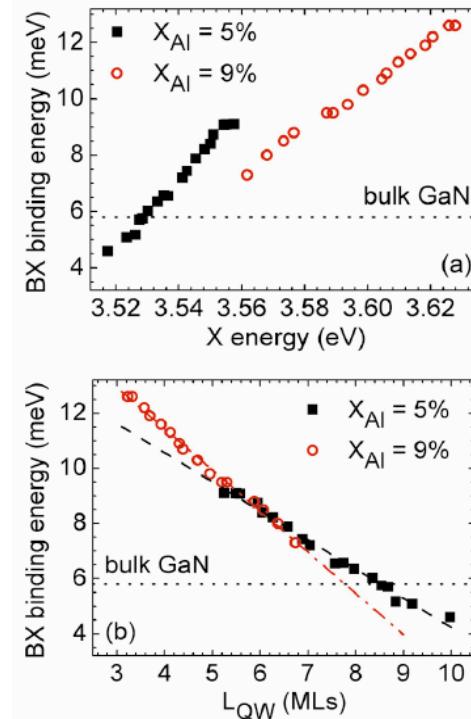
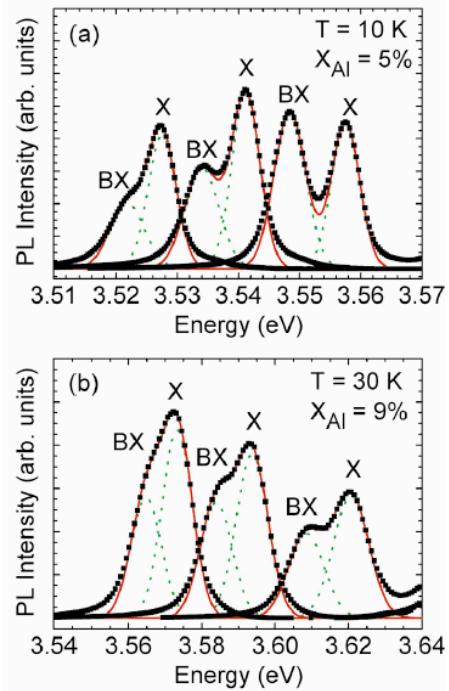
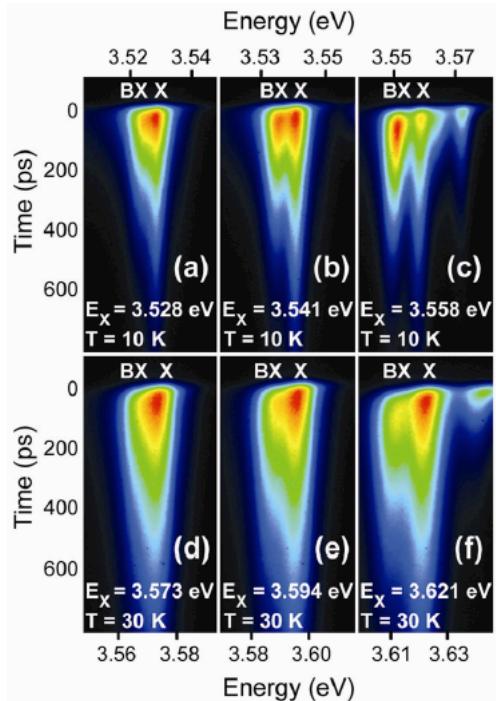
PHYSICAL REVIEW B 77, 125342 (2008)

Biexciton kinetics in GaN quantum wells: Time-resolved and time-integrated photoluminescence measurements

Flavian Stokker Cheregi,¹ Anna Vinattieri,¹ Eric Feltin,² Dobri Simeonov,² Jean-François Carlin,² Raphaël Butté,² Nicolas Grandjean,² and Massimo Gurioli¹

¹Department of Physics and LENS, Università di Firenze, 50019 Sesto Fiorentino, Italy

²Institute of Quantum Electronics and Photonics, Ecole Polytechnique Fédérale de Lausanne, CH-1015 Lausanne, Switzerland



The biexciton binding energy increases with increasing quantum confinement. For low quantum confinement values, the BX binding energy is found to decrease in the $\text{GaN}/\text{Al}_{0.05}\text{Ga}_{0.95}\text{N}$ QW below that of bulk GaN. This result is a fingerprint of the strong QCSE present in these structures.

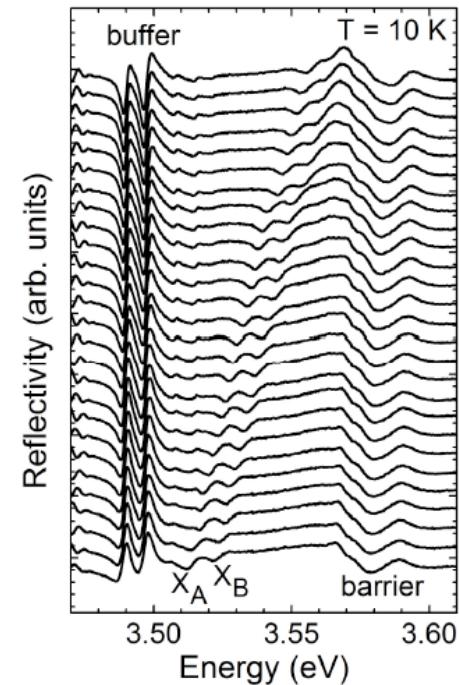
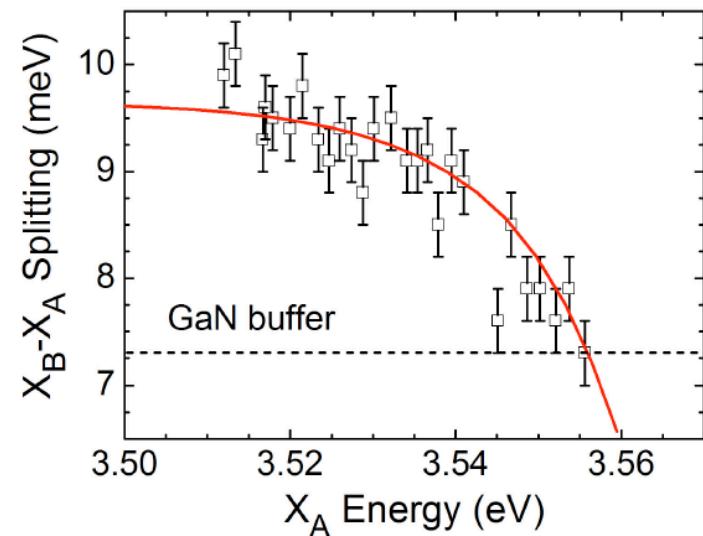
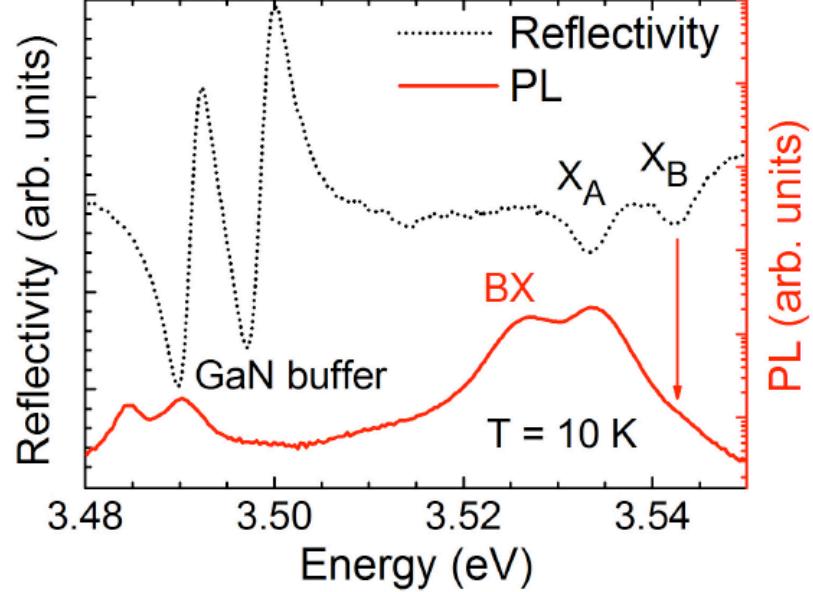
APPLIED PHYSICS LETTERS 93, 152105 (2008)

Impact of quantum confinement and quantum confined Stark effect on biexciton binding energy in GaN/AlGaN quantum wells

F. Stokker-Cheregi,^{1,a)} A. Vinattieri,¹ E. Felin,² D. Simeonov,² J. Levrat,² J.-F. Carlin,² R. Butté,² N. Grandjean,² and M. Gurioli¹

¹LENS and Department of Physics, University of Florence, I-50019 Sesto Fiorentino, Italy

²Institute of Quantum Electronics and Photonics, Ecole Polytechnique Fédérale de Lausanne, CH-1015 Lausanne, Switzerland



When decreasing the well thickness, while the energies of both X_A and X_B increase, X_B approaches the barrier limit before X_A does, so that the electron and hole wavefunctions for X_B are more sensitive to delocalization effects outside the well region making the overall energy enhancement due to the increase in quantum confinement smaller than for X_A .

PHYSICAL REVIEW B 79, 245316 (2009)

Quantum confinement dependence of the energy splitting and recombination dynamics of A and B excitons in a GaN/AlGaN quantum well

F. Stokker-Cheregi*
Department of Lasers, NILPRP, Magurele, 077125 Bucharest, Romania

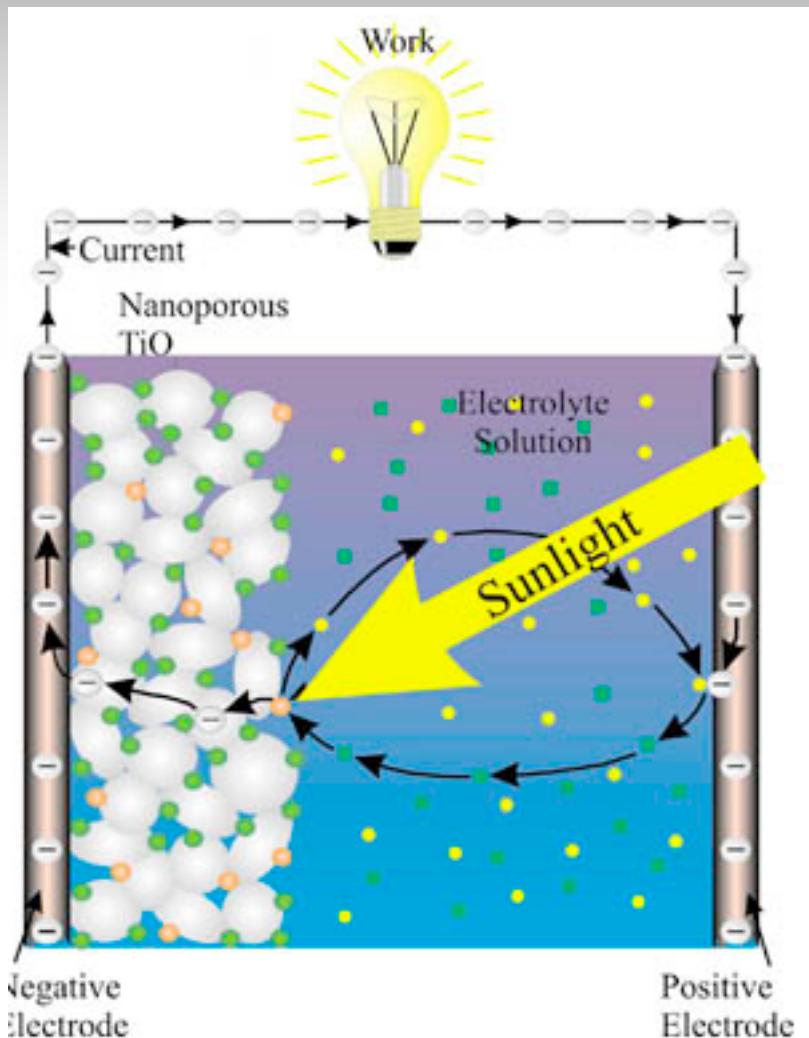
A. Vinattieri
Department of Physics and LENS, University of Florence, Sesto, I-50019 Fiorentino, Italy

E. Feltin, D. Simeonov, J.-F. Carlin, R. Butté, and N. Grandjean
Institute of Quantum Electronics and Photonics, Ecole Polytechnique Fédérale de Lausanne, CH-1015 Lausanne, Switzerland

F. Sacconi, M. Povolotskyi, and A. Di Carlo
Department of Electronic Engineering, University of Rome "Tor Vergata," 00133 Rome, Italy

M. Gurioli
Department of Physics and LENS, University of Florence, Sesto, I-50019 Fiorentino, Italy

Nanoparticles for dye-sensitized solar cells



Graetzel, Nature 414, 338 (2001)

$$\eta \approx 11\%$$

www.konarka.com

Open questions

- Charge collection & transport
- Solar spectrum coverage
- Lifetime (dye & electrolyte)

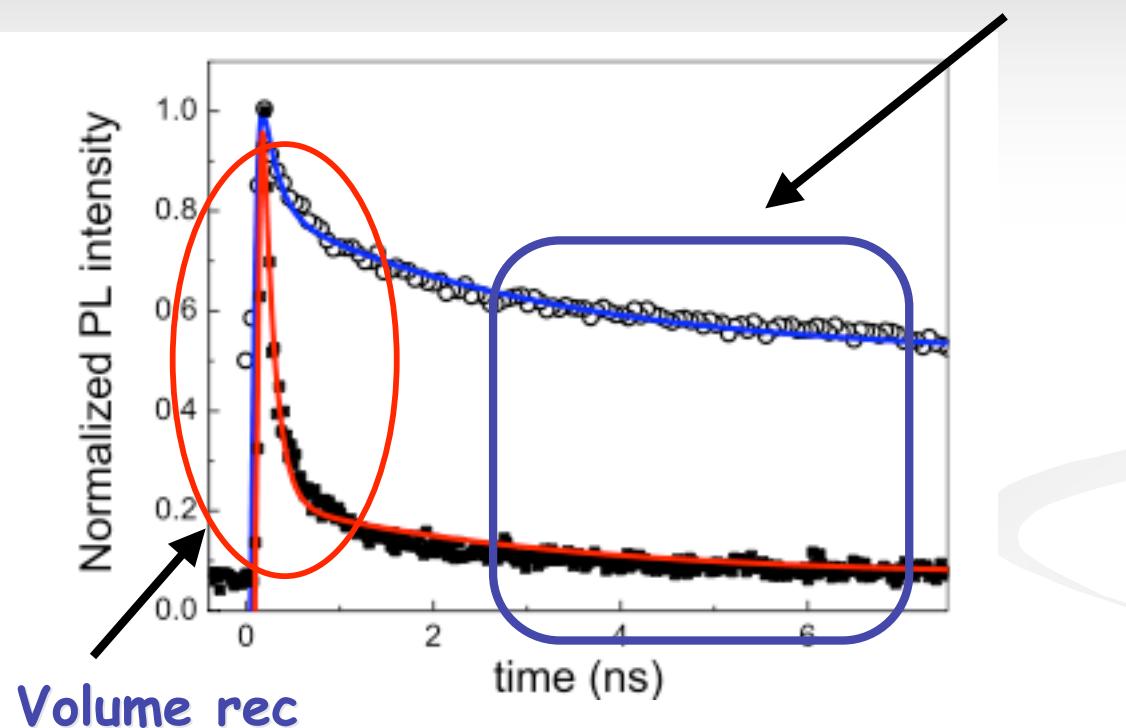
It's necessary to understand the physics of charge transfer and transport in the semiconductor mesoporous strate

Surface vs Volume contributions

Controlling the surface state recombination

Modifying the NPs environment and size

Surface rec



JOURNAL OF APPLIED PHYSICS 106, 053516 (2009)

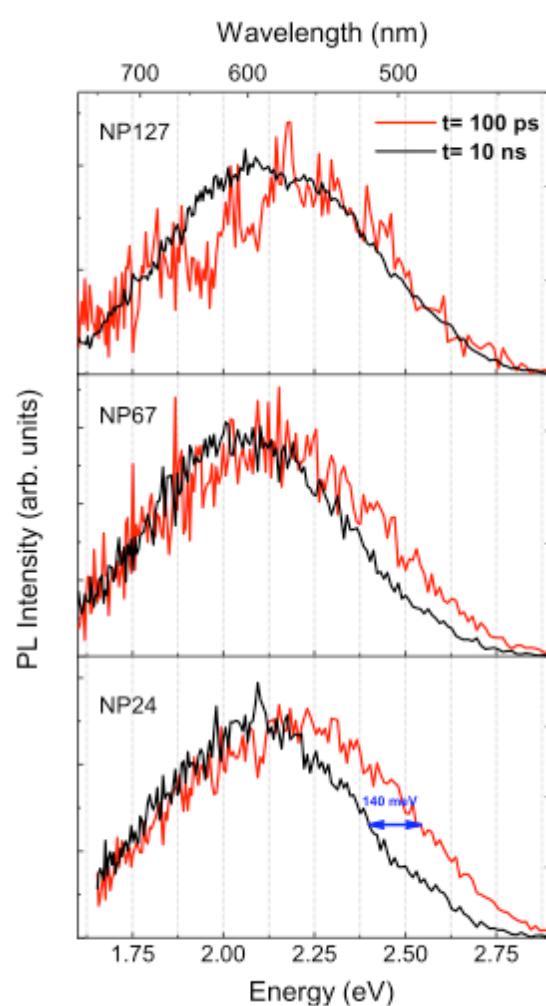
Volume versus surface-mediated recombination in anatase TiO₂ nanoparticles

Lucia Cavigli,^{1,a)} Franco Bogani,¹ Anna Vinattieri,² Valentina Faso,³ and Giovanni Baldi³

¹Dipartimento di Energetica, Università di Firenze, I-50134 Firenze, Italy

²Dipartimento di Fisica, CNISM, and LENS, Università di Firenze, I-50019 Sesto Fiorentino (Firenze), Italy

³Centro Ricerche Colorobbia (Ce.Ri.Col.) Italia, I-50053 Sovigliana-Vinci (Firenze), Italy



Work in progress

- **Nitride heterostructures: Exciton-phonon interaction**

L.Cavigli et al: Probing the exciton density of states through the phonon assisted emission in GaN epilayers: the A and B exciton contribution, PRB under submission

- **NPs for DSSC: Nanostructuring of the Semiconductor**

layer - Nanorods, Nanotubes, CNTs scaffolds (PoliTO, CNR-Pi)

F. STOKKER-CHEREGI; A. VINATTIERI; E. FELTIN; D. SIMEONOV; J.-F. CARLIN; R. BUTTÉ; N. GRANDJEAN; F. SACCONI; M. POVOLOTSKYI; A. DI CARLO; M. GURIOLI. **QUANTUM CONFINEMENT DEPENDENCE OF THE ENERGY SPLITTING AND RECOMBINATION DYNAMICS OF A AND B EXCITONS IN A GAN/ALGAN QUANTUM WELL.** PHYS.REV.B79 (2009)

L. CAVIGLI, F. BOGANI, A. VINATTIERI, V. FASO, G. BALDI. **VOLUME VERSUS SURFACE-MEDIATED RECOMBINATION IN ANATASE TIO₂ NANOPARTICLES.** JOURN.APPL.PHYS. 106, 053516 (2009)

R. MATA, N. GARRO, A. CROS, J. A. BUDAGOSKY, A. GARCÍA-CRISTÓBAL, A. VINATTIERI, M. GURIOLI, S. FOUNTA, E. BELLET-AMALRIC, B. DAUDIN. **ANISOTROPIC POLARIZATION OF NON-POLAR GAN QUANTUM DOT EMISSION.** PHYSICA STATUS SOLIDI C, 6, S541(2009)

F. STOKKER-CHEREGI, A. VINATTIERI, E. FELTIN, D. SIMEONOV, J.-F. CARLIN, R. BUTTHE', N. GRANDJEAN, M. GURIOLI. **BIEXCITON KINETICS IN GAN QUANTUM WELLS: TIME-RESOLVED AND TIME-INTEGRATED PHOTOLUMINESCENCE MEASUREMENTS.** PHYS. REV. B77, 125342 (2008)

F. STOKKER-CHEREGI; A. VINATTIERI; E. FELTIN; D. SIMEONOV; J. LEVRAT; J. F. CARLIN; R. BUTTHE'; N. GRANDJEAN; M. GURIOLI. **IMPACT OF QUANTUM CONFINEMENT AND QUANTUM CONFINED STARK EFFECT ON BIEXCITON BINDING ENERGY IN GAN/ALGAN QUANTUM WELLS.** APPL. PHYS. LETT., 93, 152105 (2008)

F. STOKKER-CHEREGI; A. VINATTIERI; F. SEMOND; M. LEROUX; I.R. SELLERS; J. MASSIES; D. SOLNYSHKOV; G. MALPUECH; M. COLOCCI; M. GURIOLI. **POLARITON RELAXATION BOTTLENECK AND ITS THERMAL SUPPRESSION IN BULK GAN MICROCAVITIES.** APPL. PHYS. LETT. 92, 042119 (2008).

F. STOKKER-CHEREGI; A. VINATTIERI; E. FELTIN; D. SIMEONOV; J.-F. CARLIN; R. BUTTHE'; N. GRANDJEAN; M. GURIOLI. **TEMPERATURE DEPENDENCE OF THE POLARITON RELAXATION BOTTLENECK IN A GAN MICROCAVITY.** PHYSICA STATUS SOLIDI. C 5, 2257 (2008)

F. STOKKER-CHEREGI; A. VINATTIERI ; E. FELTIN; D. SIMEONOV; J.-F. CARLIN; R. BUTTHE'; N. GRANDJEAN; M. GURIOLI. **BIEXCITON RECOMBINATION IN HIGH QUALITY GAN/ALGAN QUANTUM WELLS.** PHYSICA STATUS SOLIDI. C 5, 2254 (2008).

M. GURIOLI, M. ZAMFIRESCU, F. STOKKER, A. VINATTIERI, I. SELLERS, F. SEMOND, J. MASSIES, **POLARITON EMISSION IN BULK GAN MICROCAVITIES, SUPERLATTICES AND MICROSTRUCTURES,** 41, 284 (2007)

F. STOKKER-CHEREGI, M. ZAMFIRESCU, A. VINATTIERI, M. GURIOLI, I. SELLERS, F. SEMOND, M. LEROUX, J. MASSIES, **POLARITON THERMALIZATION IN GAN MICROCAVITIES IN STRONG LIGHT-MATTER COUPLING REGIME,** SUPERLATTICES AND MICROSTRUCTURES, 41, 376 (2007)

SELLERS IR; SEMOND F; ZAMFIRESCU M; STOKKER-CHEREGI F DISSEIX P; LEROUX M; LEYMARIE J; GURIOLI M; A. VINATTIERI; REVERET F; MALPUECH G; VASSON A . MASSIES J. **FROM EVIDENCE OF STRONG LIGHT-MATTER COUPLING TO POLARITON EMISSION IN GAN MICROCAVITIES.** PHYSICA STATUS SOLIDI B1882 -1896, 244 (2007)

SELLERS IR, SEMOND F, LEROUX M, MASSIES J., ZAMFIRESCU M., STOKKER-CHEREGI F., GURIOLI M., VINATTIERI A., COLOCCI M., TAHRAOUI A., KHALIFA A.A, **POLARITON EMISSION AND REFLECTIVITY IN GAN MICROCAVITIES AS A FUNCTION OF ANGLE AND TEMPERATURE,** PHYS. REV.B 74 , 193308 (2006)

□